## Gabriel Vanko

## List of Publications by Year in descending order

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1163117 1125743 25 179 8 13 citations h-index g-index papers 25 25 25 227 citing authors all docs docs citations times ranked

#	Article	IF	CITATIONS
1	Additive Manufacturing in Atomic Layer Processing Mode. Small Methods, 2022, 6, e2101546.	8.6	6
2	Uncooled Antenna-Coupled Microbolometer for Detection of Terahertz Radiation. Journal of Infrared, Millimeter, and Terahertz Waves, 2021, 42, 462-478.	2.2	6
3	Influence of SiON interlayer on the diamond/GaN heterostructures studied by Raman and SIMS measurements. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2021, 273, 115434.	3.5	0
4	Fabrication of Diamond Membranes by Femtosecond Laser Ablation for MEMS Sensor Applications. Proceedings (mdpi), 2020, 56, .	0.2	0
5	Direct Deposition of CVD Diamond Layers on Top of GaN Membranes. Proceedings (mdpi), 2020, 56, .	0.2	O
6	Carbide-free one-zone sulfurization method grows thin MoS2 layers on polycrystalline CVD diamond. Scientific Reports, 2019, 9, 2001.	3.3	19
7	Study on electronic properties of diamond/SiNx-coated AlGaN/GaN high electron mobility transistors operating up to 500 °C. Diamond and Related Materials, 2018, 89, 266-272.	3.9	9
8	Ir/Al multilayer Gates for High Temperature Operated AlGaN/GaN HEMTs. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700691.	1.8	3
9	Temperature-dependent stress in diamond-coated AlGaN/GaN heterostructures. Materials and Design, 2016, 106, 305-312.	7.0	8
10	Diamond-coated three-dimensional GaN micromembranes: Effect of nucleation and deposition techniques. Physica Status Solidi (B): Basic Research, 2015, 252, 2585-2590.	1.5	7
11	GaN/SiC based surface acoustic wave structures for hydrogen sensors with enhanced sensitivity. Sensors and Actuators A: Physical, 2015, 227, 55-62.	4.1	15
12	Influence of Diamond CVD Growth Conditions and Interlayer Material on Diamond/GaN Interface. Materials Science Forum, 2015, 821-823, 982-985.	0.3	7
13	Enhanced Sensitivity of Pt/NiO Gate Based AlGaN/GaN C-HEMT Hydrogen Sensor. Key Engineering Materials, 2014, 605, 491-494.	0.4	1
14	Selective area deposition of diamond films on AlGaN/GaN heterostructures. Physica Status Solidi (B): Basic Research, 2014, 251, 2574-2580.	1.5	15
15	Pt/NiO ring gate based Schottky diode hydrogen sensors with enhanced sensitivity and thermal stability. Sensors and Actuators B: Chemical, 2014, 202, 1-8.	7.8	14
16	4H-SiC and novel SI GaAs-based M-S-M radiation hard photodetectors applicable in UV, EUV, and soft x-ray detection: design, technology, and performance testing. Proceedings of SPIE, 2013, , .	0.8	0
17	Bulk micromachining of SiC substrate for MEMS sensor applications. Microelectronic Engineering, 2013, 110, 260-264.	2.4	31
18	Impact of Ir gate interfacial oxide layers on performance of AlGaN/GaN HEMT. Applied Surface Science, 2013, 267, 159-163.	6.1	6

#	Article	lF	CITATIONS
19	MEMS pressure sensor fabricated by advanced bulk micromachining techniques. Proceedings of SPIE, 2013, , .	0.8	1
20	AlGaN/GaN Based SAW-HEMT Devices for Chemical Gas Sensors Operating in GHz Range. Procedia Engineering, 2011, 25, 1101-1104.	1.2	4
21	AlGaN/GaN C-HEMT structures for dynamic stress detection. Sensors and Actuators A: Physical, 2011, 172, 98-102.	4.1	20
22	AlGaN/GaN C-HEMT structures for dynamic stress detection. Procedia Engineering, 2010, 5, 1405-1408.	1.2	1
23	Ohmic contacts to p-GaN Using Au/Ni-Mg-O Metallization. Journal of Electrical Engineering, 2010, 61, 378-381.	0.7	4
24	Microwave Characterization and Properties of $2\hat{l}^{1}\!/4$ m Gate Length AlGaN/GaN HEMT Structures. , 2008, , .		0
25	Modal Analysis of Gallium Nitride Membrane for Pressure Sensing Device. Key Engineering Materials, 0, 605, 404-407.	0.4	2